- **Built-In Biasing Resistors**
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)

P/N	R1 (NOM)	R2 (NOM)	MARKING
DCX122LH	0.22KΩ	10KΩ	C81
DCX142JH	0.47 K Ω	10KΩ	C82
DCX122TH	0.22 K Ω	OPEN	C83
DCX142TH	0.47 K Ω	OPEN	C84

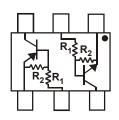
Mechanical Data

- Case: SOT-563
- Case Material: Molded Plastic; UL Flammability Classification Rating 94V-0

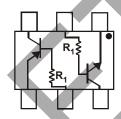
SMALL SIGNAL DUAL TRANSISTOR IN SOT563

- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Annealed over Copper Leadframe; Solderable per MIL-STD-202, Method 208@3
- Terminal Connections: See Diagram
- Weight: 0.005 grams (Approximate)

SOT-563







R₁ Only

SCHEMATIC DIAGRAM, TOP VIEW

Ordering Information (Note 4)

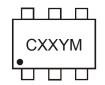
Device	Packaging	Shipping
DCX122LH-7	SOT-563	3,000/Tape & Reel
DCX142JH-7	SOT-563	3,000/Tape & Reel
DCX122TH-7	SOT-563	3,000/Tape & Reel
DCX142TH-7	SOT-563	3,000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.</p>
 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information

SOT-563



CXX = Product Type Marking Code YM = Date Code Marking Y = Year ex: T = 2006 M = Month ex: 9 = September

Date Code Kev

Year	2002	2003	2004	2005	2006	2007	2008	2009	2010	2011	2012
Code	N	Р	R	S	Т	U	V	W	Х	Y	Z

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



Maximum Ratings NPN Section (@T_A = +25°C unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Supply Voltage		V _{CC}	50	V
Input Voltage	DCX122LH DCX142JH	V _{IN}	-5 to +6 -5 to +6	V
Input Voltage	DCX122TH DCX142TH	V _{EBO} (MAX)	5	V
Output Current	All	Ic	100	mA
Power Dissipation	(Notes 5 & 6)	P _d	150	mW
Thermal Resistance, Junction to Ambient Air	(Note 5)	$R_{\theta JA}$	833	°C/W
Operating and Storage Temperature Range		T _j , T _{STG}	-55 to +150	°C

Maximum Ratings PNP Section (@T_A = +25°C unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Supply Voltage		Vcc	-50	V
Input Voltage	DCX122LH DCX142JH	V _{IN}	+5 to -6 +5 to -6	V
Input Voltage	DCX122TH DCX142TH	VEBO (MAX)	-5	V
Output Current	All	Ic	-100	mA
Power Dissipation	(Notes 5 & 6)	P_d	150	mW
Thermal Resistance, Junction to Ambient Air	(Note 5)	$R_{ hetaJA}$	833	°C/W
Operating and Storage Temperature Range		T _j , T _{STG}	-55 to +150	°C

Notes:

- Mounted on FR4 PC Board with recommended pad layout at http://www.diodes.com/datasheets/ap02001.pdf.
 NPN Section, PNP Section, or maximum combined.





Electrical Characteristics NPN Section, R1, R2 Types (@TA = +25°C unless otherwise specified.)

Characteristic		Symbol	Min	Тур	Max	Unit	Test Condition
Input Voltage	DCX122LH DCX142JH	$V_{I(off)}$	0.3 0.3	_	_	٧	V _{CC} = 5V, I _O = 100μA
gs	DCX122LH DCX142JH	V _{I(on)}			2.0 2.0	٧	V _O = 0.3V, I _O = 20mA V _O = 0.3V, I _O = 20mA
Output Voltage		$V_{O(on)}$			0.3V	٧	$I_{O}/I_{I} = 5mA/0.25mA$
Input Current	DCX122LH DCX142JH	l _l	_	_	28 13	mA	V _I = 5V
Output Current		I _{O(off)}		_	0.5	μА	$V_{CC} = 50V, V_{I} = 0V$
DC Current Gain	DDCX122LH DDCX142JH	Gı	56 56				V _O = 5V, I _O = 10mA
Gain-Bandwidth Product*		f _T		200		MHz	V _{CE} = 10V, I _E = 5mA, f = 100MHz

^{*} Transistor - For Reference Only

Electrical Characteristics NPN Section, R1-Only (@TA = +25°C unless otherwise specified.)

Characteristic		Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Base Breakdown Voltage		BV _{CBO}	50		_	V	I _C = 50μA
Collector-Emitter Breakdown Voltage		BV _{CEO}	40	_	_	V	I _C = 1mA
Emitter-Base Breakdown Voltage DCX122TH DCX142TH		BV _{EBO}	5			V	I _E = 50μA I _E = 50μA
Collector Cut-Off Current		I _{CBO}	_	_	0.5	μΑ	V _{CB} = 50V
Emitter Cut-Off Current	DCX122TH DCX142TH	I _{EBO}			0.5 0.5	μA	V _{EB} = 4V
Collector-Emitter Saturation Voltage		V _{CE(sat)}			0.3	V	I _C = 5mA, I _B = 0.25mA
DC Current Transfer Ratio	DCX122TH DCX142TH	h _{FE}	100 100	250 250	600 600		I _C = 1mA, V _{CE} = 5V
Gain-Bandwidth Product*		f⊤	_	200	_	MHz	V _{CE} = 10V, I _E = -5mA, f = 100MHz

^{*} Transistor - For Reference Only

Electrical Characteristics PNP Section, R1, R2 Types (@TA = +25°C unless otherwise specified.)

Characteristic		Symbol	Min	Тур	Max	Unit	Test Condition
Input Voltage	DCX122LH DCX142JH	$V_{I(off)}$	-0.3 -0.3		_	٧	V _{CC} = -5V, I _O = -100μA
put voitago	DCX122LH DCX142JH	V _{I(on)}			-2.0 -2.0	V	$V_O = -0.3V$, $I_O = -20mA$ $V_O = -0.3V$, $I_O = -20mA$
Output Voltage		$V_{O(on)}$		_	-0.3V	V	$I_{O}/I_{I} = -5$ mA/-0.25mA
Input Current	DCX122LH DCX142JH	l _l			-28 -13	mA	V ₁ = -5V
Output Current		I _{O(off)}	_	_	-0.5	μΑ	V _{CC} = -50V, V _I = 0V
DC Current Gain	DCX122LH DCX142JH	G _l	56 56		_	_	V _O = -5V, I _O = -10mA
Gain-Bandwidth Product*		f⊤		200	_	MHz	V _{CE} = -10V, I _E = -5mA, f = 100MHz

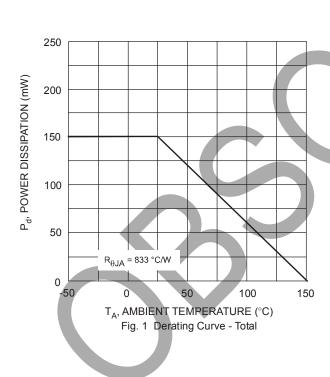
^{*} Transistor - For Reference Only



Electrical Characteristics, R1-Only Types @TA = 25°C unless otherwise specified

Characteristic		Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Base Breakdown Voltage		BV_CBO	-50		_	V	I _C = -50μA
Collector-Emitter Breakdown Voltage		BV _{CEO}	-40	_	_	V	I _C = -1mA
Emitter-Base Breakdown Voltage	DCX122TH DCX142TH	BV _{EBO}	-5		_	V	I _E = -50μA I _E = -50μA
Collector Cut-Off Current		I _{CBO}			-0.5	μΑ	V _{CB} = -50V
Emitter Cut-Off Current	DCX122TH DCX142TH	I _{EBO}			-0.5 -0.5	μΑ	V _{EB} = -4V
Collector-Emitter Saturation Voltage		V _{CE(sat)}			-0.3	٧	$I_C = -5mA$, $I_B = -0.25mA$
DC Current Transfer Ratio	DCX122TH DCX142TH	h _{FE}	100 100	250 250	600 600		I _C = -1mA, V _{CE} = -5V
Gain-Bandwidth Product*		f⊤	_	200	_	MHz	V _{CE} = -10V, I _E = 5mA, f = 100MHz

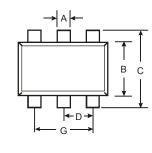
^{*} Transistor - For Reference Only

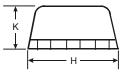


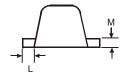


Package Outline Dimensions

Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



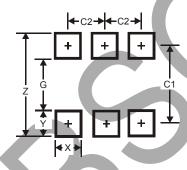




	SO	T563	
Dim	Min	Max	Тур
Α	0.15	0.30	0.20
В	1.10	1.25	1.20
С	1.55	1.70	1.60
D	-	-	0.50
G	0.90	1.10	1.00
Н	1.50	1.70	1.60
K	0.55	0.60	0.60
L	0.10	0.30	0.20
М	0.10	0.18	0.11
All	Dimens	sions in	mm

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
Z	2.2
G	1.2
X	0.375
Y	0.5
C1	1.7
C2	0.5



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